



# 7/B 2826  
2/26/03  
Muelis

Atty. Docket No. 8013-1070

PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Takao ARAI

Serial No. 09/963,533

Filed September 27, 2001

Confirmation No. 9250

GROUP 2826

Examiner Johannes P. Mondt

SEMICONDUCTOR DEVICE INCLUDING A  
DEPLETION TYPE LATERAL MOSFET AND  
METHOD OF FORMING THE SAME

AMENDMENT

Commissioner for Patents

Washington, D.C. 20231

Sir:

Responsive to the Official Action of November 18, 2002,  
please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 5, replace the paragraph, beginning on line 9,  
bridging pages 5 and 6, as follows:

B1  
--With reference to FIG. 1I, the resist patterns 35,  
the gate electrodes 30a, 30b and 30c and the field oxide films 26  
are used as masks for selective ion-implantation of arsenic as an  
n-type impurity into selected regions in the p-well region 25 and  
in the p+-type regions 34 at a high impurity concentration. The  
used resist patterns 35 are completely removed. A heat treatment  
is then carried out for activation of the implanted impurity,  
thereby to selectively form n+-type regions 36a, 36b, 36c and 36d  
in the p-well region 25, and n+-type regions 36e in the p+-type

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